

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10635	((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/03 19:49
L2	3814	((photo near2 resist) near2 (layer or film)) same ((photo near2 mask\$1) or mask\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 19:14
L3	31804	ldd or (lightly near2 dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:43
L4	56	2 same 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:43
L5	8	1 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:45
L6	48	4 not 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:49
L7	56	((photo near2 resist) near2 (layer or film)) same ((photo near2 mask\$1) or mask\$1) same (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:52
L8	23	((photo near2 resist) near2 (layer or film)) same ((photo near2 mask\$1) or mask\$1) near10 (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:56
L9	6	(pattern\$3 near5 ((photo near2 resist) near2 (layer or film))) near10 (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:58

L10	2575	(pattern\$3 near5 ((photo near2 resist) near2 (layer or film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:58
L11	31	10 same 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:58
L28	6545	pattern\$3 near5 (photo near2 resist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 19:59
L29	77	28 same (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 19:16
L30	11	29 and 1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 19:17
L31	66	29 not 30	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 19:17
L32	10933	((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/180) or (438/181) or (438/197) or (438/301) or (438/364) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/03 19:54
L33	181	32 and 28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 20:00
L34	58	33 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 20:01

S1	10043	((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/03 18:30
S2	30291	ldd or (lightly near2 dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:42
S3	3632	(photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/03 18:31
S4	16861	((poly near2 crystall\$3) or poly) near2 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:09
S5	458116	tft or (thin near2 film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:15
S6	337	(ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 19:39
S7	10	((((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 19:55

S8	1	((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.) and (((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 19:40
S9	5	((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 19:55
S10	38	((ldd or (lightly near2 dop\$3)) and ((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1))) and (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:06
S11	2	((((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:07

S12	11	((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)) and (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:08
S13	64	((photo near2 resist) near2 (layer or film) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:16
S14	10301	(source same drain) near10 (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:16
S15	803	((source same drain) near10 (ldd or (lightly near2 dop\$3))) and (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:17
S16	372	((source same drain) near10 (ldd or (lightly near2 dop\$3))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:17
S17	56	((source same drain) near10 (ldd or (lightly near2 dop\$3))) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:17
S18	3093	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:07
S19	159	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:29

S20	13	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:26
S21	0	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.) not ((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:29
S22	146	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) not (((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) and ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:29

S23	31623	((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:14
S24	104	((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same ((source same drain) near10 (ldd or (lightly near2 dop\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:42
S25	10	((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same ((source same drain) near10 (ldd or (lightly near2 dop\$3)))) and (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:44
S26	136	((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:44
S27	31	((((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) same (((poly near2 crystall\$3) or poly) near2 silicon)) and (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:44
S28	30	((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:51
S29	117	((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:55
S30	36	((((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:52

S31	31	(((((photo near2 resist) or resist) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)) not (((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1)) near10 ((source and drain) and (ldd or (lightly near2 dop\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:52
S32	307	((photo near2 resist) or resist) near10 (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:56
S33	198	((photo near2 resist) or resist) near5 (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:58
S34	9	(((((photo near2 resist) or resist) near5 (((poly near2 crystall\$3) or poly) near2 silicon)) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 20:56
S35	229	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:22

S36	6	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$)) and (idd or (lightly near2 dop\$3))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:09
S37	73	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((ion near2 implant\$4) or dop\$)) and (idd or (lightly near2 dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:10
S38	56	((photo near2 resist) or resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:17
S39	7	((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:18
S40	94	((photo near2 resist) or resist) near5 (layer or film) same ((photo near2 mask\$1) or mask\$1) near10 ((poly near2 crystall\$3) or poly) near2 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:19
S41	157	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:31
S42	10	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$)) and (((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:25

S43	48	((photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$)) and (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:25
S44	1	(photo near2 resist) near5 (pattern\$3) same ((photo near2 mask\$1) or mask\$1) near5 ((ion near2 implant\$4) or dop\$) same ((poly near2 crystall\$3) or poly) near2 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/10 21:32
S45	20174	((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:56
S46	16861	((poly near2 crystall\$3) or poly) near2 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:10
S47	303223	(ion near2 implant\$4) or dop\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:16
S48	124	((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) same ((poly near2 crystall\$3) or poly) near2 silicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:14
S49	84	((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) same ((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:18
S50	511	((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and ((poly near2 crystall\$3) or poly) near2 silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:14
S51	391	((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and ((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:14

S52	458116	tft or (thin near2 film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:15
S53	191	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:47
S54	10043	((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/11 11:15
S55	19	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:16

S56	172	(((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:34
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S57	0	(((((((photo near2 resist) or (photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 (photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not ((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))) not ((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:34
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S58	219	((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not (((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:35
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S59	200	<p>(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) not ((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) not ((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and ((ion near2 implant\$4) or dop\$3)) and (tft or (thin near2 film))) and (((438/149) or (438/151) or (438/163) or (438/164) or (438/166) or (438/197) or (438/301) or (438/365) or (438/369) or (438/486) or (438/488) or (438/491) or (438/514) or (435/552) or (438/708) or (438/725) or (438/736) or (438/737)).CCLS.))) not ((((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film)))</p>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:47
S60	215	<p>(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near10 ((photo near2 mask\$1) or mask\$1)) and (((poly near2 crystall\$3) or poly) near2 silicon)) and (tft or (thin near2 film))</p>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:49
S61	16906	<p>((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near5 ((photo near2 mask\$1) or mask\$1)</p>	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:57

S62	1373	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near5 ((photo near2 mask\$1) or mask\$1)) same (tft or (thin near2 film)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:58
S63	507	(((((photo near2 resist) or ((photo or light) near2 sensitive) or resist) near2 (layer or film)) near5 ((photo near2 mask\$1) or mask\$1)) same (tft or (thin near2 film))) and ((ion near2 implant\$4) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 11:59
S64	5	("5037766" "5372958" "5462887" "5504019" "5529937").PN.	USPAT	OR	OFF	2004/08/11 12:29
S65	2	("5985741" "6066547").PN.	USPAT	OR	OFF	2004/08/11 12:39
S66	18	("4549843" "4655874" "4676868" "4764483" "4824802" "4865952" "4902899" "4952274" "5077234" "5110410" "5139608" "5175122" "5286581" "5296092" "5310621" "5350486" "5362591" "5418093").PN.	USPAT	OR	OFF	2004/08/11 12:42
S67	5	("5412493" "5736751" "5962916" "6365936" "6384427").PN.	USPAT	OR	OFF	2004/08/11 12:44
S68	1	"6624443".URPN.	USPAT	OR	OFF	2004/08/11 12:45
S69	3	("4231811" "5985766" "6043000").PN.	USPAT	OR	OFF	2004/08/11 12:46
S70	0	"6410211".URPN.	USPAT	OR	OFF	2004/08/11 12:46
S71	9	("3920483" "3997367" "4035226" "4137458" "4140913" "4144101" "4149904" "4163155" "4182023").PN.	USPAT	OR	OFF	2004/08/11 12:47
S72	155	((ldd or (lightly near2 dop\$3)) same (source and drain)) near10 simultan\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 14:27
S73	65	((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 simultan\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 14:32
S74	91	((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 (simultan\$6 or "same" adj time)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 14:33

S75	26	((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 (simultan\$6 or "same" adj time)) not ((ldd or (lightly near2 dop\$3)) same (source and drain)) near5 simultan\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/08/11 14:33
S76	2	"6452241".URPN.	USPAT	OR	OFF	2004/08/11 14:35
S77	2	("5914498" "6259120").PN.	USPAT	OR	OFF	2004/08/11 14:36